

Supplementary Information

**Magnetic-mesoporous Janus nanoparticles**

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Figure S1. TEM image of the silica nanorods synthesized without  $\text{Fe}_3\text{O}_4$  NP substrates, showing a relative large size-distribution.

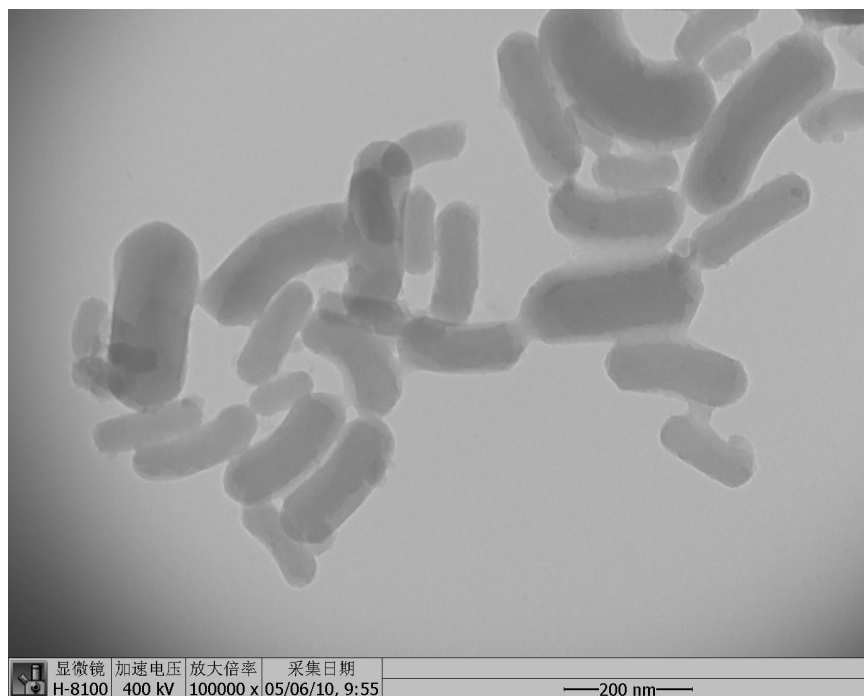
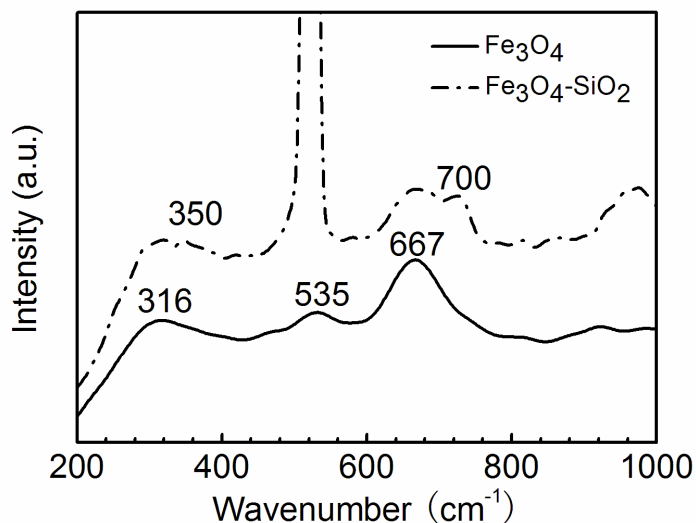


Figure S2. Raman spectra of Fe<sub>3</sub>O<sub>4</sub> nanoparticles and Fe<sub>3</sub>O<sub>4</sub>-SiO<sub>2</sub> Janus particles.



Raman spectra were recorded by a OMATS89 Raman spectrometer (JY Company, France) with 514 nm argon ion laser as excitation source. The figure below is the Raman spectrum of initial magnetic iron oxide nanoparticles and Janus particles. In the Raman spectra of Fe<sub>3</sub>O<sub>4</sub>, there exhibit three clear peaks at 667, 535 and 316 cm<sup>-1</sup>, which can be indexed to the A<sub>1g</sub>, T<sub>2g</sub> and E<sub>g</sub> modes of Fe<sub>3</sub>O<sub>4</sub>, respectively. For Fe<sub>3</sub>O<sub>4</sub>-SiO<sub>2</sub> Janus particles, except the Raman shift of Fe<sub>3</sub>O<sub>4</sub>, two weak peaks appearing at 700 and 350 cm<sup>-1</sup> are the characteristic bands of  $\gamma$ -Fe<sub>2</sub>O<sub>3</sub>. Because Fe<sub>3</sub>O<sub>4</sub> particles can be partially oxidized into  $\gamma$ -Fe<sub>2</sub>O<sub>3</sub> in the course of washing and preserving. The marked increase of Raman shift at about 500 nm<sup>-1</sup> was due to the silicon substrate.